

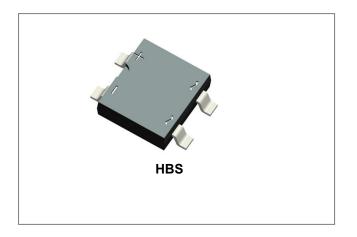
HBN802 THRU HBN810

RoHS

Technical Data Data Sheet N2771, Rev. -

HBN802 THRU HBN810

Glass Passivated Single-Phase 8.0Amp Surface Mount Bridge Rectifier



Features

- Surface mount bridge, small package;
- Ideal for printed circuit boards;
- Glass passivated chip junction;
- High forward current capability up to 8.0A;
- High surge current capability;
- High heat dissipation capability;
- Low profile package;
- Low forward voltage drop;
- Plastic package has Underwrites Laboratory Flammability Classification 94V-0
- This is a Pb Free Device
- All SMC parts are traceable to the wafer lot
- Additional testing can be offered upon request

Mechanical Data

- Case: HBS;
- Epoxy meets UL-94V-0 Flammability rating;
- Terminals:Matte tin plated leads, solderable per J-STD-002 and JESD22-B102;
- High temperature soldering guaranteed: Solder Reflow 260℃,10seconds;
- Polarity: As marked on body;
- Marking: Type number;

Maximum Ratings and Electrical Characteristics @T_A=25°C unless otherwise specified

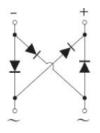
Single Phase half wave 60Hz, resistive or inductive load. For capacitive load current derate by 20%.

Type Number	Symbol	HBN802	HBN804	HBN806	HBN808	HBN810	Units
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage	V _{RRM} V _{RWM} V _{DC}	200	400	600	800	1000	V
RMS Reverse Voltage	V _{RMS}	140	280	420	560	700	V
Maximum average forward rectified output current at $@T_A = 25^{\circ}C$	I _(AV)	8				Α	
Non-Repetitive Peak Forward Surge Current 8.3ms Single half sine-wave superimposed on rated load (JEDEC Method)	I _{FSM}	160				A	
Rating for fusing (t<8.3ms)	l²t	106				A ² sec	

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Circuit Diagram





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Fig. 2 Typ. Forward Characteristics

Electrical Characteristics@T_A=25°C unless otherwise specified

Type Number	Symbol	HBN802	HBN804	HBN806	HBN808	HBN810	Units
Maximum Forward Voltage (per element) @I⊧ =4A @I⊧ =8A	V _F	1.0 1.1			V		
Maximum Peak Reverse Current $@T_A = 25^{\circ}C$ At Rated DC Blocking Voltage $@T_A = 125^{\circ}C$	I _R	5 200			μA		
Typical capacitance(Note 1)	Cj	52			pF		

* Pulse width < 300 μ s, duty cycle < 2%

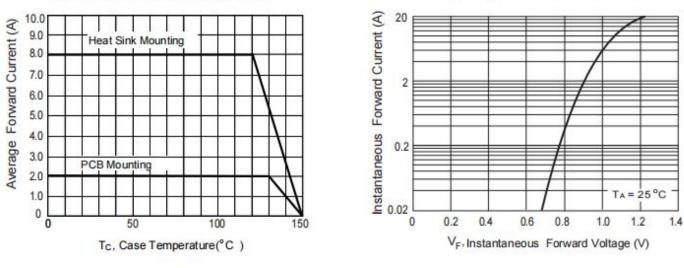
Thermal-Mechanical Specifications@T_A=25°C unless otherwise specified

Type Number	Symbol	HBN802	HBN804	HBN806	HBN808	HBN810	Units
Typical Thermal Resistance	R _{θJA} Rθjc Rθjl	70.0 10.0 14.0			°C/W		
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150			°C		

Note: 1. Mounted at 1.0 MHz and applied reverse voltage of 5.0V DC;

Ratings and Characteristics Curves

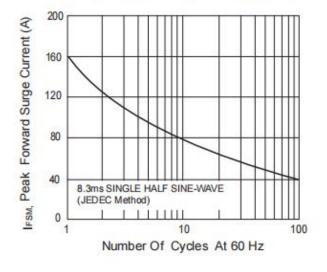




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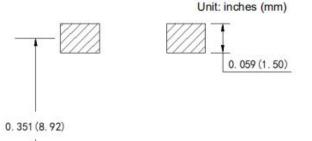


Fig. 3 Max Non-Repetitive Peak Fwd Surge Current



1000 Instantaneous Reverse Current (uA) 100 10 TA=125°C 1.0 0.1 T_=25°C = 0.01 0 20 40 60 80 100 Percent Of Rated Peak Reverse Voltage (%)

Suggested PCB printfoot layout



0.078(2.0)

0.138 (3.50)

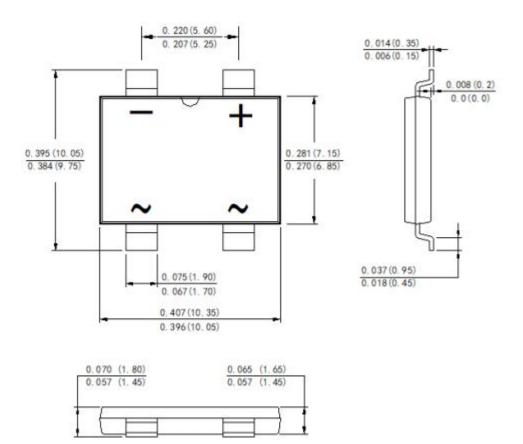




Fig.4 Typical Reverse Chracteristics



Mechanical Dimensions HBS(Inches/Millimeters)

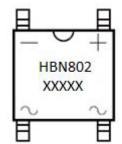


Ordering Information

Device	Package	Plating	Shipping
HBN802 THRU HBN810	HBS (Pb-Free)	Pure Sn	2500pcs / reel

For information on tape and reel specifications, including part orientation and tape sizes, please refer to our tape and reel packaging specification.

Marking Diagram



Where XXXXX is YYWWL

HBN802 = Type Number YΥ

ww

L

- = Year
- = Week = Lot Number

Cautions: Molding resin Epoxy resin UL:94V-0

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